



SuperSOT4™ DUAL 12V PNP SILICON LOW SATURATION SWITCHING TRANSISTOR

SUMMARY

 V_{ceo} =-12V; R_{sat} = 47m Ω ; I_c = -3A

DESCRIPTION

This new 4th generation ultra low saturation transistor utilises the Zetex matrix structure combined with advanced assembly techniques to give extremely low on state losses. This makes it ideal for high efficiency, low voltage switching applications.

MSOP8

FEATURES

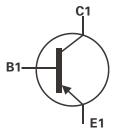
- Extremely Low Equivalent On Resistance
- Extremely Low Saturation Voltage
- h_{FF} characterised up to 12A
- I_C=3A Continuous Collector Current
- MSOP8 package

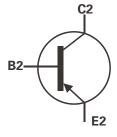
APPLICATIONS

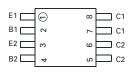
- DC DC Converters
- Power Management Functions
- · Power switches
- Motor control

ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXT12P12DXTA	7	12mm embossed	1000 units
ZXT12P12DXTC	13	12mm embossed	4000 units







Top View

DEVICE MARKING

T12P12DX

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-12	V
Emitter-Base Voltage	V _{EBO}	-7.5	V
Peak Pulse Current	I _{CM}	-15	А
Continuous Collector Current	I _C	-3	А
Base Current	I _B	-500	mA
Power Dissipation at TA=25°C (a)(d) Linear Derating Factor	P _D	0.87 6.9	W mW/°C
Power Dissipation at TA=25°C (a)(e) Linear Derating Factor	P _D	1.04 8.3	W mW/°C
Power Dissipation at TA=25°C (b)(d) Linear Derating Factor	P _D	1.25 10	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

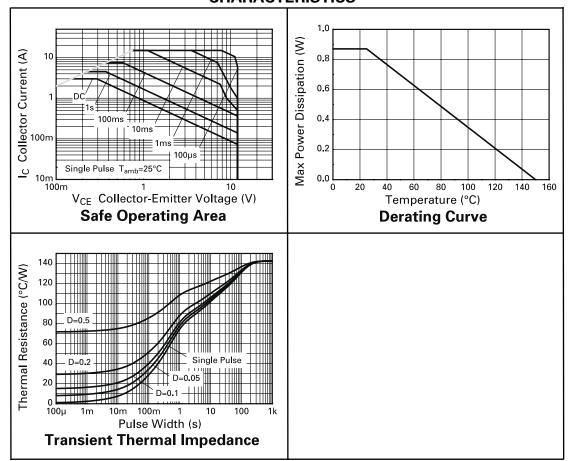
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	143	°C/W
Junction to Ambient (b)(d)	$R_{ heta JA}$	100	°C/W
Junction to Ambient (a)(e)	$R_{\theta JA}$	120	°C/W

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- (b) For a device surface mounted on FR4 PCB measured at t≤5 secs.
- (c) Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
- (d) For device with one active die.
- (e) For device with two active die running at equal power.



CHARACTERISTICS





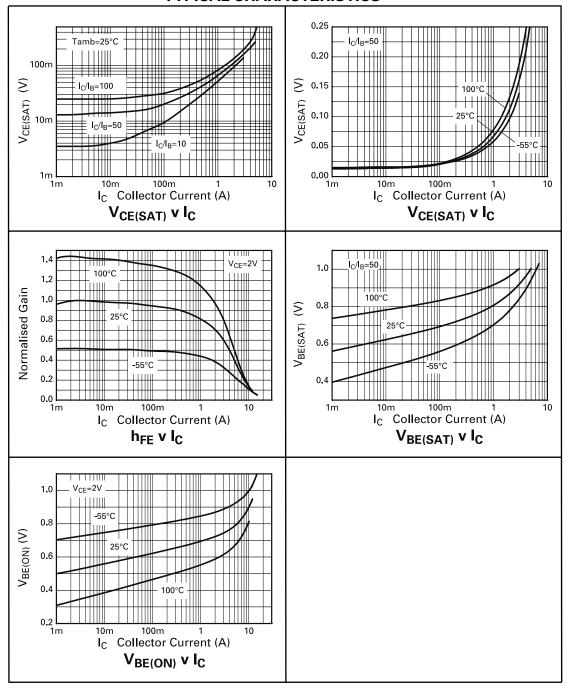
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	-35		V	I _C =-100μA	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-12	-28		V	I _C =-10mA*	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-7.5	-8.5		V	Ι _Ε =-100μΑ	
Collector Cut-Off Current	I _{CBO}			-100	nA	V _{CB} =-16V	
Emitter Cut-Off Current	I _{EBO}			-100	nA	V _{EB} =-6V	
Collector Emitter Cut-Off Current	I _{CES}			-100	nA	V _{CES} =-16V	
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-8 -65 -195 -140	-11 -85 -270 -190	mV mV mV	I _C =-0.1A, I _B =-10mA* I _C =-1A, I _B =20mA* I _C =-3A, I _B =-30mA* I _C =-3A, I _B =-150mA*	
Base-Emitter Saturation Voltage	V _{BE(sat)}		-0.88	-0.95	V	I _C =-3A, I _B =-30mA*	
Base-Emitter Turn-On Voltage	V _{BE(on)}		-0.84	-0.90	V	I _C =-3A, V _{CE} =-2V*	
Static Forward Current Transfer Ratio	h _{FE}	300 300 200 20	450 450 300 40	900		I _C =-10mA, V _{CE} =-2V* I _C =-1A, V _{CE} =-2V* I _C =-3A, V _{CE} =-2V* I _C =-12A, V _{CE} =-2V*	
Transition Frequency	f _T		85		MHz	I _C =-50mA, V _{CE} =-10V f=-50MHz	
Output Capacitance	C _{obo}		75		pF	V _{CB} =-10V, f=1MHz	
Turn-On Time	t _(on)		100		ns	V _{CC} =-10V, I _C =-3A I _{B1} =I _{B2} =-60mA	
Turn-Off Time	t _(off)		1710		ns		

^{*}Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq 2\%$

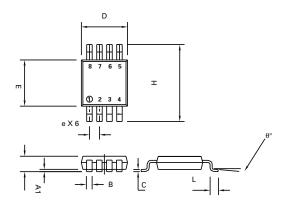


TYPICAL CHARACTERISTICS





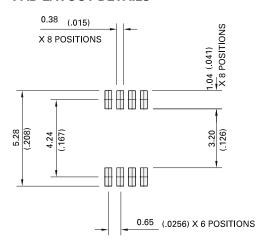
PACKAGE DIMENSIONS



Conforms to JEDEC MO-187 Iss A

DIM	Millimetres		Inches		
	MIN	MAX	MIN	MAX	
А		1.10		0.043	
A1	0.05	0.15	0.002	0.006	
В	0.25	0.40	0.010	0.016	
С	0.13	0.23	0.005	0.009	
D	2.90	3.10	0.114	0.122	
е	0.65	BSC	0.0256	BSC	
E	2.90	3.10	0.114	0.122	
Н	4.90	BSC	0.193	BSC	
L	0.40	0.70	0.016	0.028	
q°	0°	6°	0°	6°	

PAD LAYOUT DETAILS





Zetex plc. Fields New Road, Chadderton, Oldham, OL9-8NP, United Kingdom. Telephone: (44)161 622 4422 (Sales), (44)161 622 4444 (General Enquiries) Fax: (44)161 622 4420

Zetex GmbH Streitfeldstraße 19 D-81673 München Germany

Germany Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 Zetex Inc. 47 Mall Drive, Unit 4 Commack NY 11725 USA

Telephone: (631) 543-7100 Fax: (631) 864-7630 Zetex (Asia) Ltd. 3510 Metroplaza, Tower 2 Hing Fong Road, Kwai Fong, Hong Kong Telephone:(852) 26100 611 Fax: (852) 24250 494 These are supported by agents and distributors in major countries world-wide © Zetex plc 2000

Internethttp://www.zetex.com

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B